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Si3443DV

P-Channel 2.5V Specified PowerTrench® MOSFET

General Description

This P-Channel 2.5V specified MOSFET is produced using Fairchild's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain low gate charge for superior switching performance.

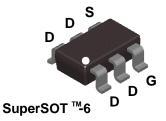
These devices have been designed to offer exceptional power dissipation in a very small footprint for applications where the larger packages are impractical.

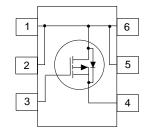
Applications

- Load switch
- · Battery protection
- Power management

Features

- -4 A, -20 V. $R_{DS(ON)} = 0.065 \Omega$ @ $V_{GS} = -4.5 V$ $R_{DS(ON)} = 0.100 \Omega$ @ $V_{GS} = -2.5 V$
- · Fast switching speed.
- · Low gate charge (7.2nC typical).
- High performance trench technology for extremely low $R_{\scriptscriptstyle DS(ON)}.$
- SuperSOT[™]-6 package: small footprint (72% smaller than standard SO-8); low profile (1mm thick).





Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		-20	V
V _{GSS}	Gate-Source Voltage		±8	V
I _D	Drain Current - Continuous	(Note 1)	-4	Α
	Drain Current - Pulsed	(Note 1a)	-20	
P _D	Power Dissipation for Single Operation	(Note 1a)	1.6	W
		(Note 1b)	0.8	1
T _J , T _{stg}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

$R_{_{\theta}JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W	
R _{eJC}	Thermal Resistance, Junction-to-Case	(Note 1)	30	°C/W	

Package Outlines and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
.443	Si3443DV	7"	8mm	3000 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics	1	II.			
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = -250 μA	-20			V
<u>ΔBV_{DSS}</u> ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = -250 μ A, Referenced to 25°C		-16		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 8 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -8 V, V _{DS} = 0 V			-100	nA
On Char	acteristics (Note 2)					
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = -250 μA	-0.4	-0.7	-1.5	V
$\Delta V_{GS(th)} = \Delta T_{,J}$	Gate Threshold Voltage Temperature Coefficient	I_D = -250 μ A, Referenced to 25°C		2.5		mV/°C
R _{DS(on)}	Static Drain-Source On-Resistance	$V_{GS} = -4.5 \text{ V}, I_D = -4 \text{ A}$ $V_{GS} = -4.5 \text{ V}, I_D = -4 \text{ A}, T_J=125^{\circ}\text{C}$ $V_{GS} = -2.5 \text{ V}, I_D = -3.2 \text{ A}$		0.054 0.076 0.077	0.065 0.105 0.100	Ω
I _{D(on)}	On-State Drain Current	V _{GS} = -4.5 V, V _{DS} = -5 V	-10			Α
g FS	Forward Transconductance	V _{DS} = -5 V, I _D = -4 A		9		S
Dynamic	: Characteristics					
C _{iss}	Input Capacitance	V _{DS} = -10 V, V _{GS} = 0 V		640		pF
Coss	Output Capacitance	f = 1.0 MHz		pF		
C _{rss}	Reverse Transfer Capacitance	1 1		90		pF
Switchin	g Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time	V _{DD} = -10 V, I _D = -1 A		11	20	ns
t _r	Turn-On Rise Time	$V_{GS} = -4.5 \text{ V}, R_{GEN} = 6 \Omega$		19	30	ns
t _{d(off)}	Turn-Off Delay Time			26	42	ns
t _f	Turn-Off Fall Time			35	55	ns
Q_g	Total Gate Charge	$V_{DS} = -10 \text{ V}, I_{D} = -4 \text{ A}$		7.2	10	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = -4.5 \text{ V},$		1.7		nC
Q _{gd}	Gate-Drain Charge	1		1.6		nC
Drain-Sc	ource Diode Characteristics and	d Maximum Ratings				
l _S	Maximum Continuous Drain-Source Did				-1.3	Α
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = -1.3 \text{ A}$ (Note 2)		-0.75	-1.2	V

Notes:

a) 78° C/W when mounted on a 1.0 in² pad of 2 oz. copper.

b) 156° C/W when mounted on a minimum pad of 2 oz.copper.

2. Pulse Test: Pulse Width $\leq\!300\,\mu\text{s},\,\text{Duty Cycle}\,\!\leq\!2.0\%$

^{1.} $R_{\theta,IA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta,IC}$ is guaranteed by design while $R_{\theta,CA}$ is determined by the user's board design.

Typical Characteristics

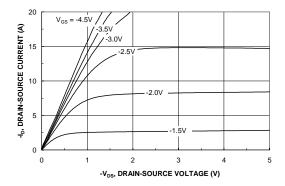


Figure 1. On-Region Characteristics.

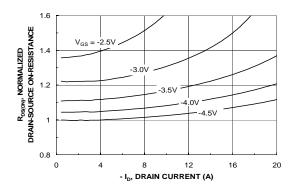


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

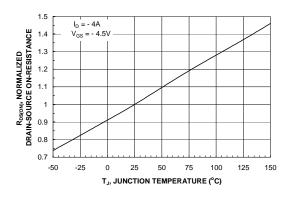


Figure 3. On-Resistance Variation with Temperature.

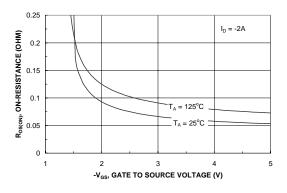


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

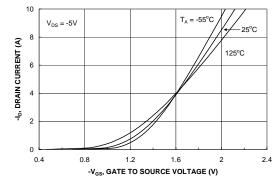


Figure 5. Transfer Characteristics.

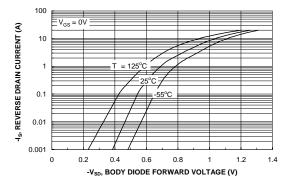
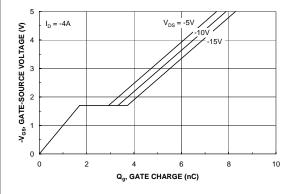


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics (continued)



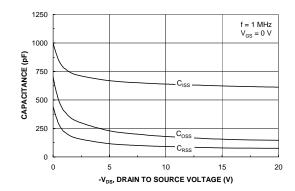
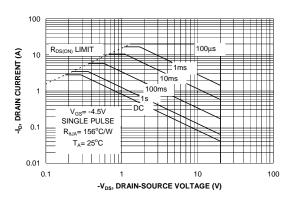


Figure 7. Gate-Charge Characteristics

Figure 8. Capacitance Characteristics



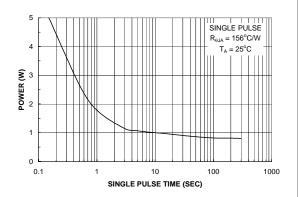


Figure 9. Maximum Safe Operating Area

Figure 10. Single Pulse Maximum Power Dissipation

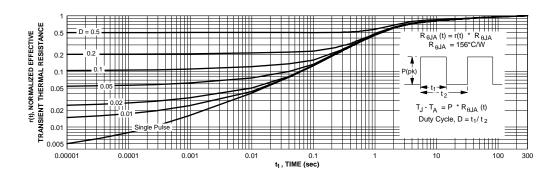


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b. Transient themal response will change depending on the circuit board design.

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Телефон: 8 (812) 309-75-97 (многоканальный)

Факс: 8 (812) 320-03-32

Электронная почта: ocean@oceanchips.ru

Web: http://oceanchips.ru/

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, д. 2, корп. 4, лит. А